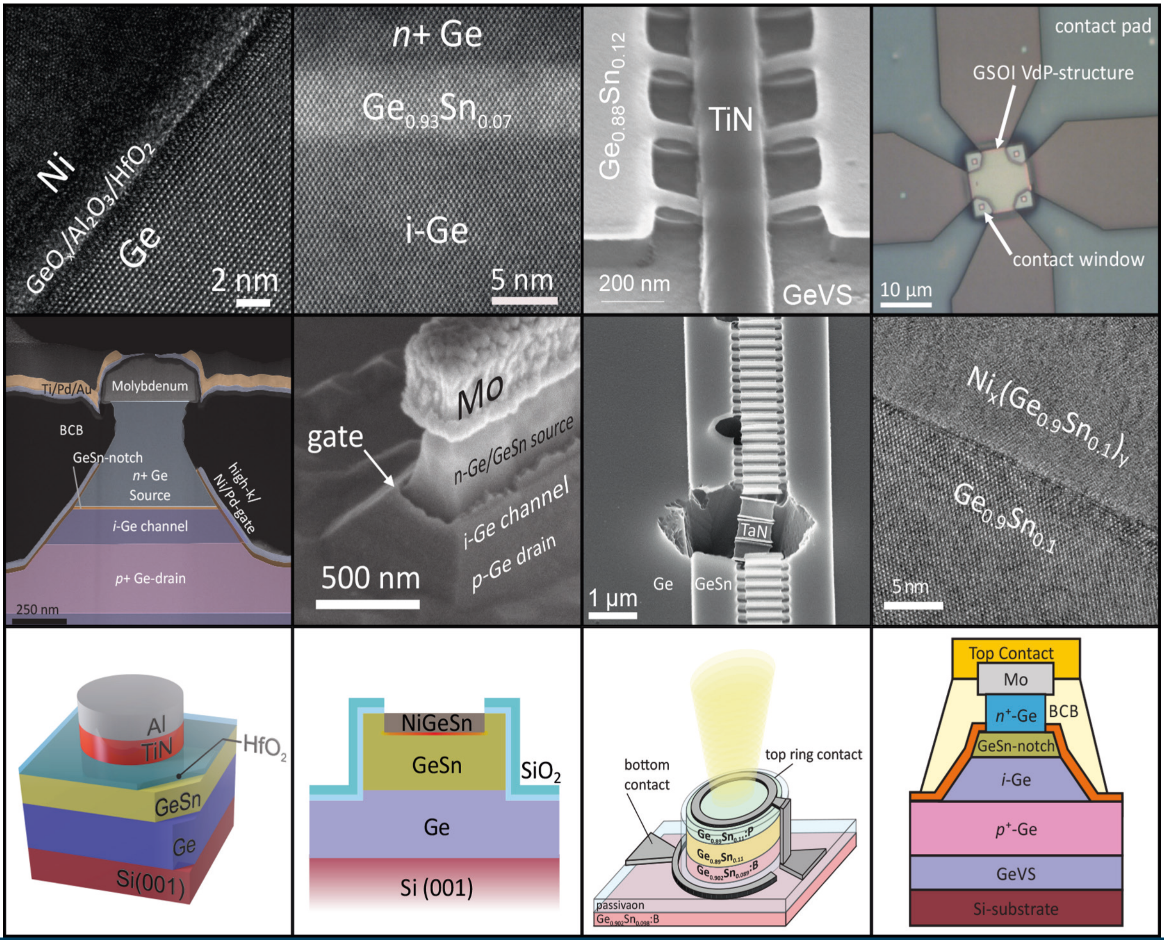

Investigation of GeSn as Novel Group IV Semiconductor for Electronic Applications

Christian Schulte-Braucks

Schlüsseltechnologien / Key Technologies
Band / Volume 168
ISBN 978-3-95806-312-9

Mitglied der Helmholtz-Gemeinschaft

JÜLICH
Forschungszentrum

Forschungszentrum Jülich GmbH
Peter Grünberg Institut
Halbleiter-Nanoelektronik (PGI-9)

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Schriften des Forschungszentrums Jülich
Reihe Schlüsseltechnologien / Key Technologies Band / Volume 168

ISSN 1866-1807 ISBN 978-3-95806-312-9

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